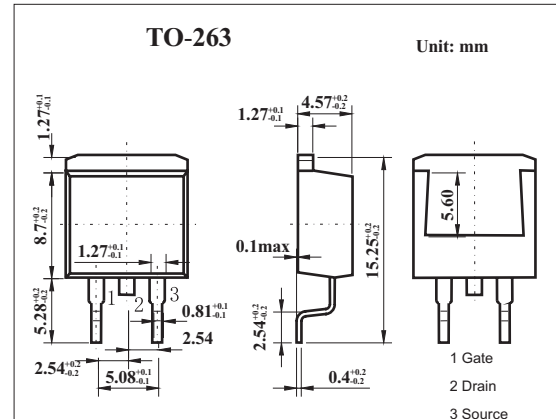


MOS Field Effect Transistor

2SK3740

■ Features

- Gate voltage rating: ± 30 V
- Low on-state resistance
 $R_{DS(on)} = 160 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 10 \text{ A)}$
- Low gate charge
 $Q_G = 47 \text{ nC TYP. (} V_{DD} = 200 \text{ V, } V_{GS} = 10 \text{ V, } I_D = 20 \text{ A)}$
- Surface mount package available



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	250	V
Gate to source voltage	V_{GS}	± 30	V
Drain current	I_D	± 20	A
	I_{DP}^*	± 60	A
Power dissipation	P_D	1.5	W
		100	
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=250\text{V}, V_{GS}=0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}, V_{DS}=0$			± 10	μA
Gate cut off voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	2.5	3.5	4.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10\text{V}, I_D=10\text{A}$	7.0	15		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		0.12	0.16	Ω
Input capacitance	C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0, f=1\text{MHz}$		1720		pF
Output capacitance	C_{oss}			330		pF
Reverse transfer capacitance	C_{rss}			170		pF
Turn-on delay time	t_{on}	$I_D=10\text{A}, V_{GS(on)}=10\text{V}, R_G=0 \Omega, V_{DD}=125\text{V}$		17		ns
Rise time	t_r			17		ns
Turn-off delay time	t_{off}			49		ns
Fall time	t_f			9		ns
Total Gate Charge	Q_G	$V_{DD} = 200\text{V}$ $V_{GS} = 10 \text{ V}$ $I_D = 20\text{A}$		47		nC
Gate to Source Charge	Q_{GS}			7		nC
Gate to Drain Charge	Q_{GD}			25		nC